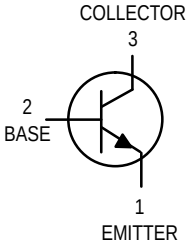
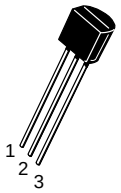
General Purpose Transistors
NPN Silicon

2N3903
2N3904*

***Motorola Preferred Device**





CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS*

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

* Indicates Data in addition to JEDEC Requirements.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	—	Vdc
Collector–Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current (V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)	I_{BL}	—	50	nAdc
Collector Cutoff Current (V_{CE} = 30 Vdc, V_{EB} = 3.0 Vdc)	I_{CEX}	—	50	nAdc

1. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

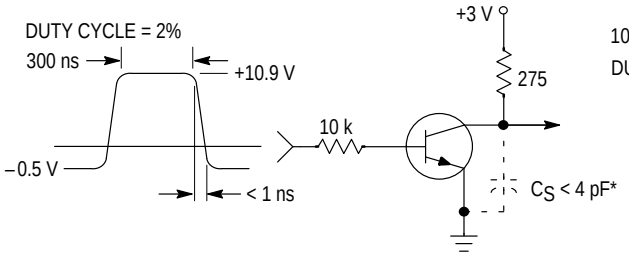
Preferred devices are Motorola recommended choices for future use and best overall value.

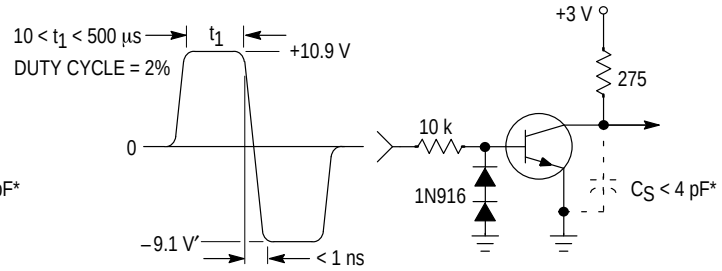
REV 2

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain(1)		h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 1.0 Vdc)	2N3903		20	—	
	2N3904		40	—	
(I_C = 1.0 mAdc, V_{CE} = 1.0 Vdc)	2N3903		35	—	
	2N3904		70	—	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	2N3903		50	150	
	2N3904		100	300	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N3903		30	—	
	2N3904		60	—	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	2N3903		15	—	
	2N3904		30	—	
Collector–Emitter Saturation Voltage(1)		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			—	0.2	
(I_C = 50 mAdc, I_B = 5.0 mAdc			—	0.3	
Base–Emitter Saturation Voltage(1)		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			0.65	0.85	
(I_C = 50 mAdc, I_B = 5.0 mAdc)			—	0.95	
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product		f_T			MHz
(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N3903		250	—	
	2N3904		300	—	
Output Capacitance		C_{obo}	—	4.0	pF
(V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)					
Input Capacitance		C_{ibo}	—	8.0	pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)					
Input Impedance		h_{ie}			k Ω
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903		1.0	8.0	
	2N3904		1.0	10	
Voltage Feedback Ratio		h_{re}			X 10^{-4}
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903		0.1	5.0	
	2N3904		0.5	8.0	
Small–Signal Current Gain		h_{fe}			—
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N3903		50	200	
	2N3904		100	400	
Output Admittance		h_{oe}	1.0	40	μmhos
(I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)					
Noise Figure		NF			dB
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k Ω, f = 1.0 kHz)	2N3903		—	6.0	
	2N3904		—	5.0	
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = 0.5 Vdc,	t_d	—	35	ns
Rise Time	I_C = 10 mAdc, I_{B1} = 1.0 mAdc)	t_r	—	35	ns
Storage Time	(V_{CC} = 3.0 Vdc, I_C = 10 mAdc, 2N3903	t_s	—	175	ns
	I_{B1} = I_{B2} = 1.0 mAdc) 2N3904		—	200	
Fall Time		t_f	—	50	ns

1. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.





* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

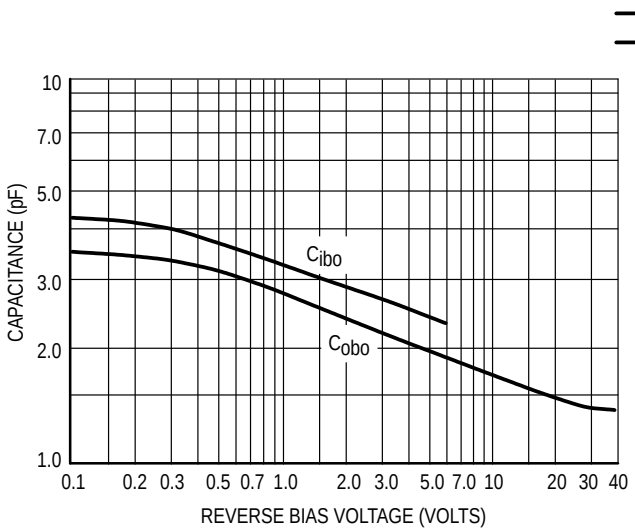


Figure 3. Capacitance

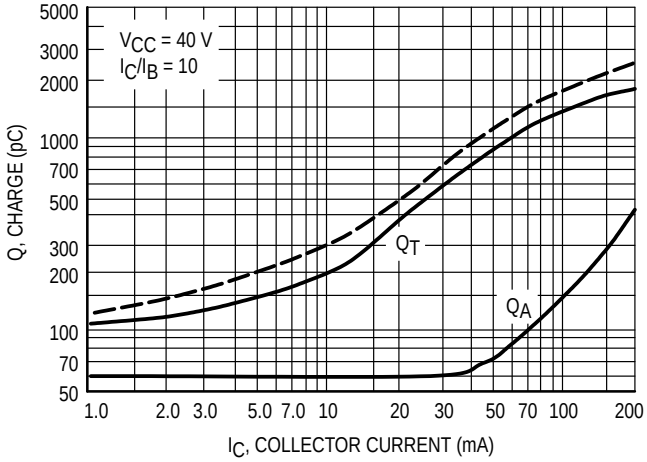


Figure 4. Charge Data

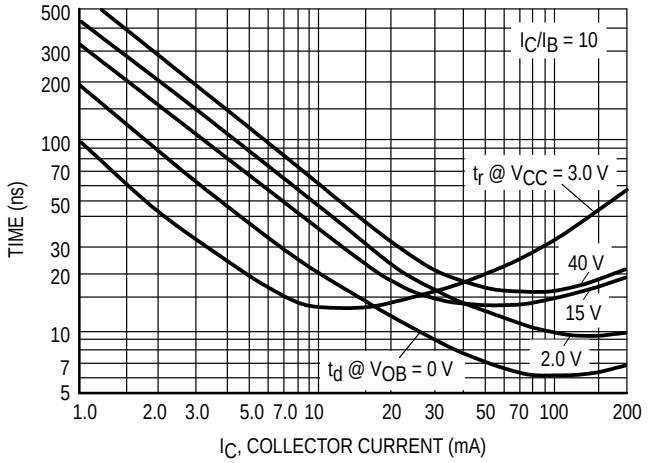


Figure 5. Turn–On Time

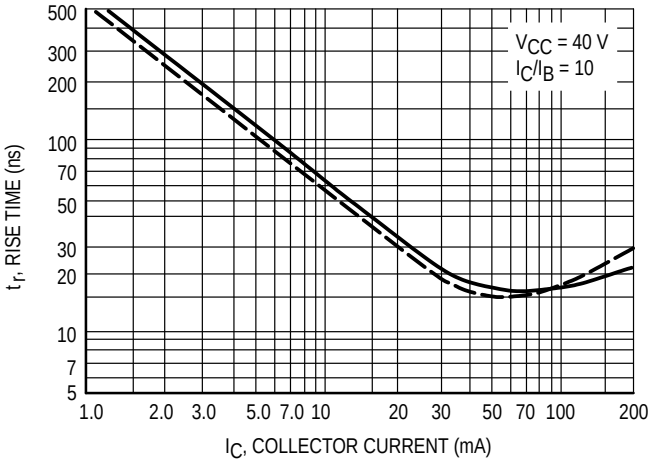


Figure 6. Rise Time

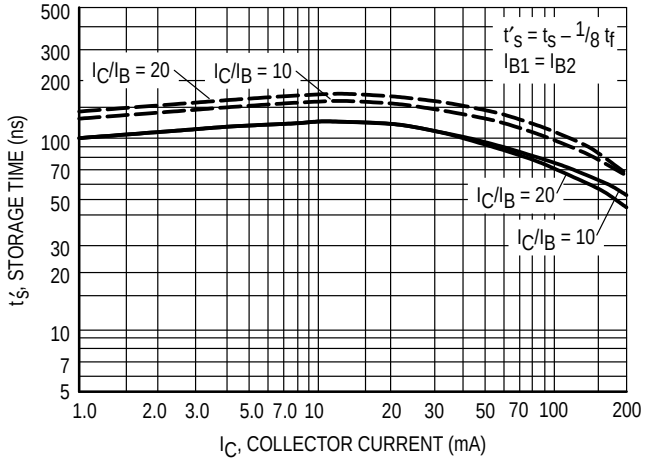


Figure 7. Storage Time

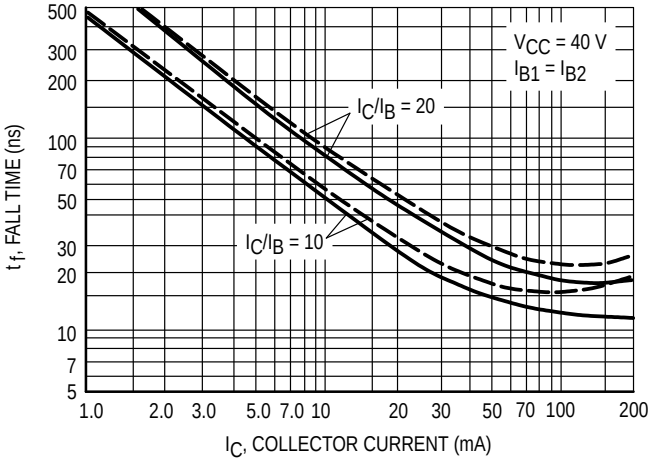


Figure 8. Fall Time

TYPICAL AUDIO SMALL–SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

(V_{CE} = 5.0 Vdc, T_A = 25°C, Bandwidth = 1.0 Hz)

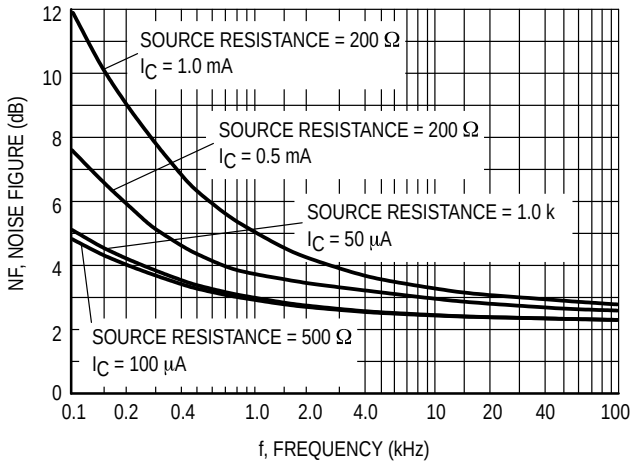


Figure 9.

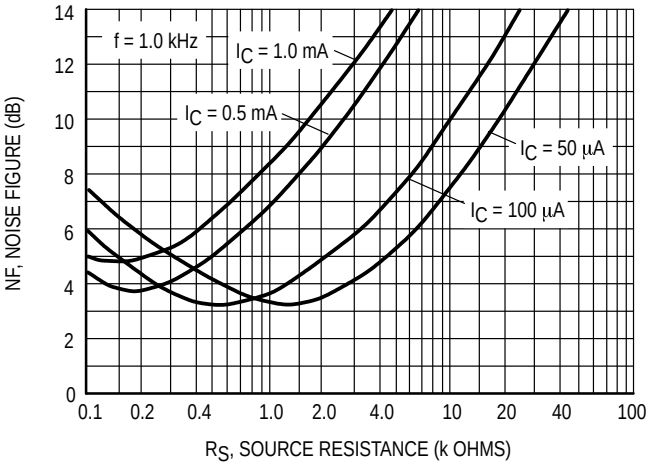


Figure 10.

h PARAMETERS

(V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C)

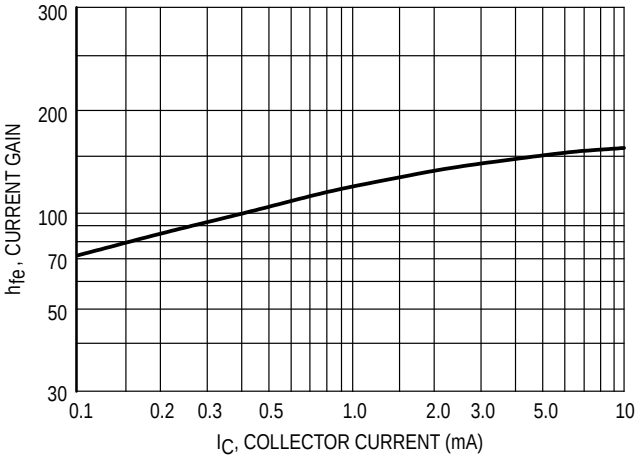


Figure 11. Current Gain

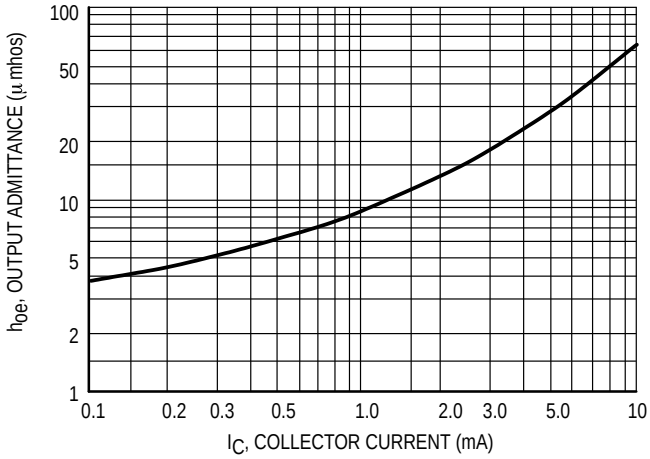


Figure 12. Output Admittance

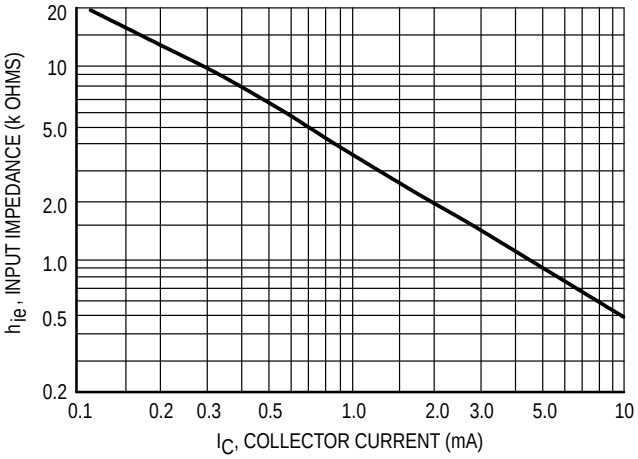


Figure 13. Input Impedance

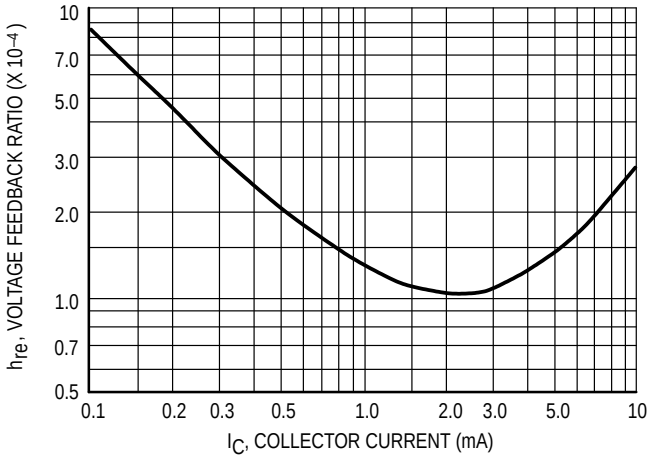


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

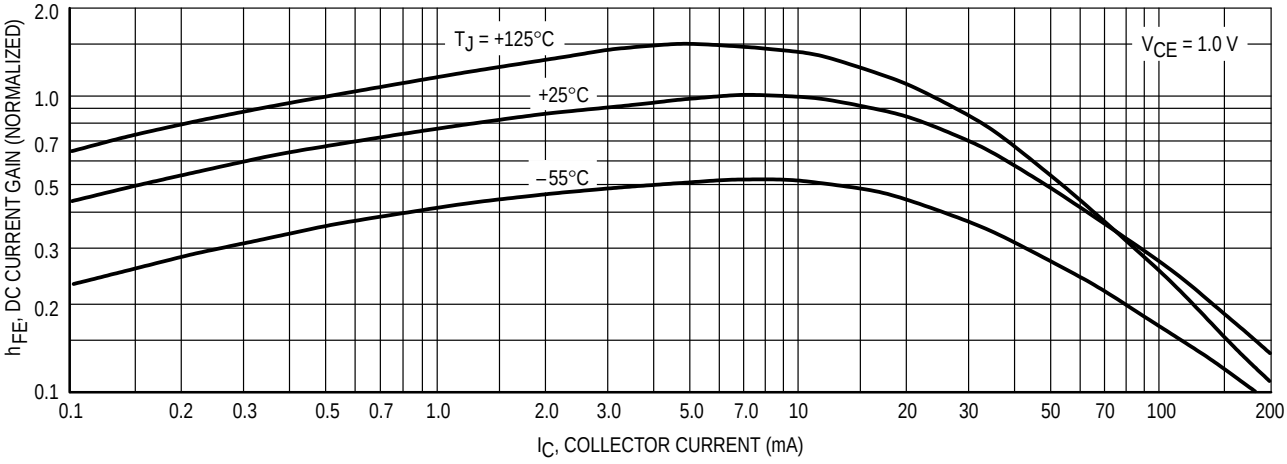


Figure 15. DC Current Gain

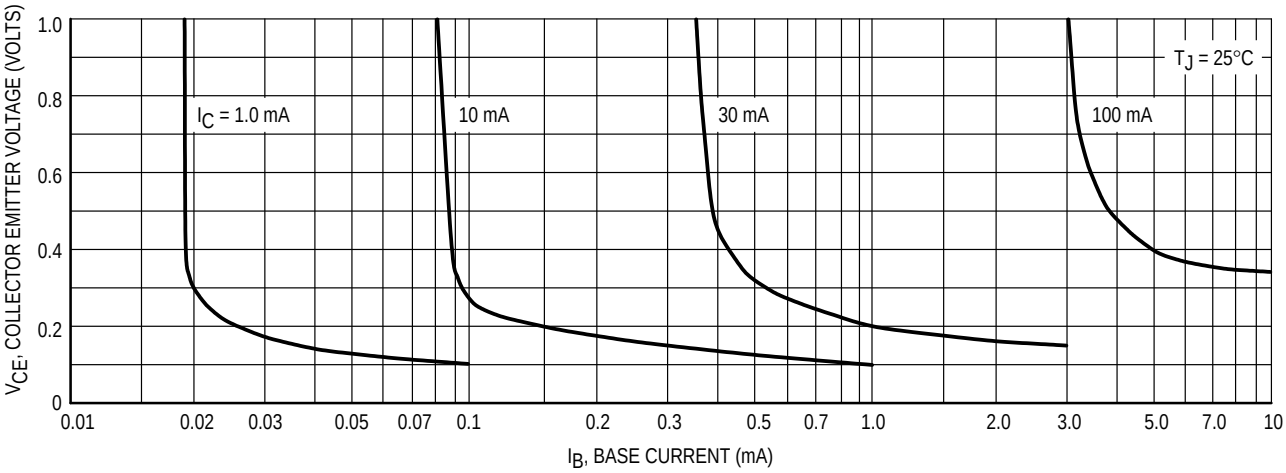


Figure 16. Collector Saturation Region

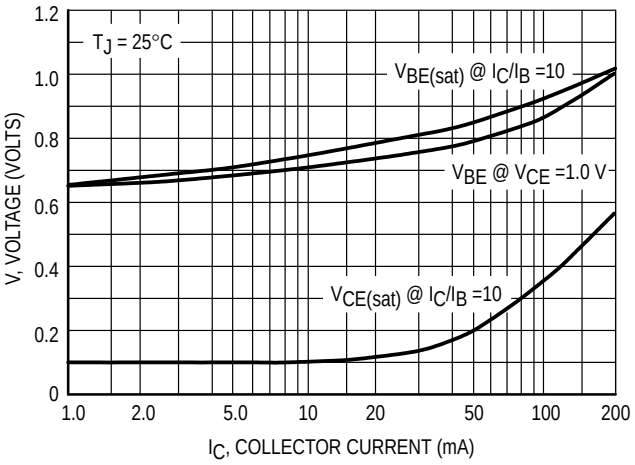


Figure 17. “ON” Voltages

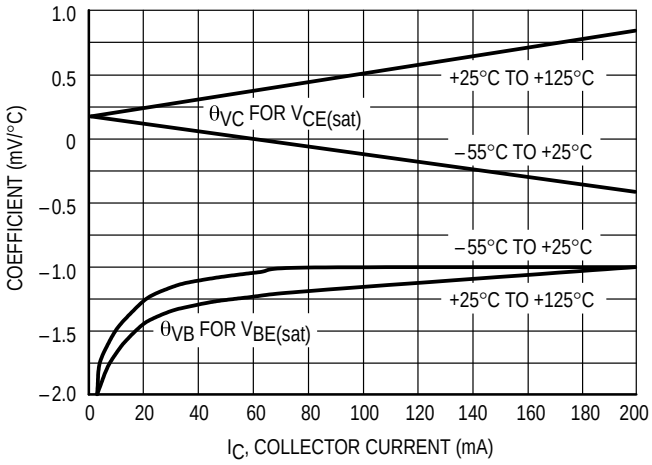
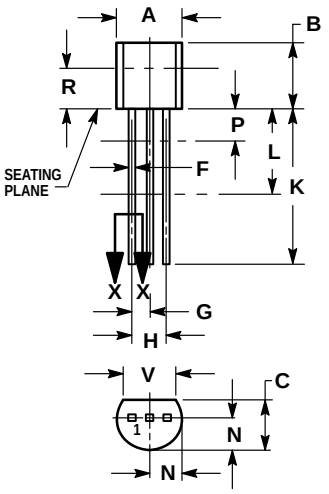
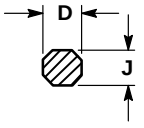


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS





SECTION X–X

CASE 029–04
(TO–226AA)
ISSUE AD

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298